

Silicon NPN Power Transistor

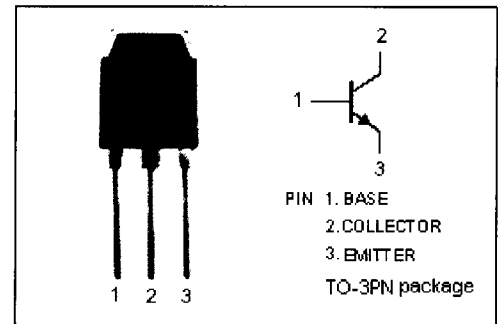
MJH16006

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
 : $V_{CEO(SUS)} = 450V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for high-voltage ,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.
 Typical applications:
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

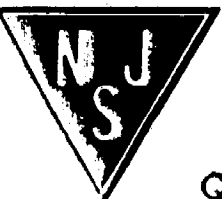
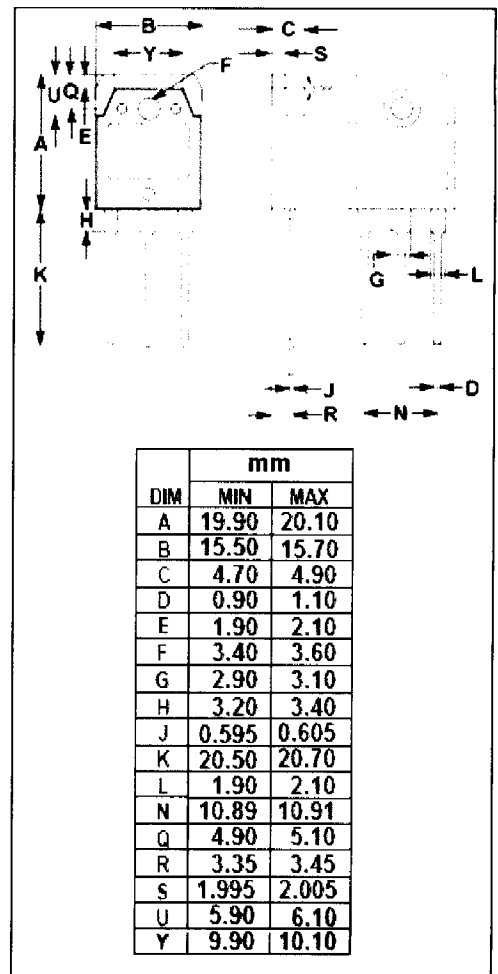


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	850	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	16	A
I_B	Base Current-Continuous	6	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	125	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.0	$^{\circ}C/W$



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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	450			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C= 3\text{A}; I_B= 0.4\text{A}$			2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C= 5\text{A}; I_B= 0.66\text{A}$ $I_C= 5\text{A}; I_B= 0.66\text{A}, T_C=100^{\circ}\text{C}$			3.0 3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 5\text{A}; I_B= 0.66\text{A}$ $I_C= 5\text{A}; I_B= 0.66\text{A}, T_C=100^{\circ}\text{C}$			1.5 1.5	V
I_{CEV}	Collector Cutoff Current	$V_{CEV}=850\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CEV}=850\text{V}; V_{BE(off)}=1.5\text{V}; T_C=100^{\circ}\text{C}$			0.25 1.5	mA
I_{CER}	Collector Cutoff Current	$V_{CE}= 850\text{V}; R_{BE}= 50\ \Omega, T_C= 100^{\circ}\text{C}$			2.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 6\text{V}; I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C= 8\text{A}; V_{CE}= 5\text{V}$	5			
C_{OB}	Output Capacitance	$I_E= 0; V_{CB}= 10\text{V}; f_{test}=1.0\text{kHz}$			350	pF

Switching times; Resistive Load

t_d	Delay Time	$I_C= 5\text{A}, V_{CC}= 250\text{V}; R_{B2}= 4\ \Omega;$ $I_{B1}= 0.66\text{A}; I_{B2}= -1.3\text{A}; \text{PW}= 30\ \mu\text{s};$ Duty Cycle $\leq 2.0\%$		20	50	ns
t_r	Rise Time			85	250	ns
t_s	Storage Time			1000	2500	ns
t_f	Fall Time			70	250	ns